Figure 1 (Prior Art)

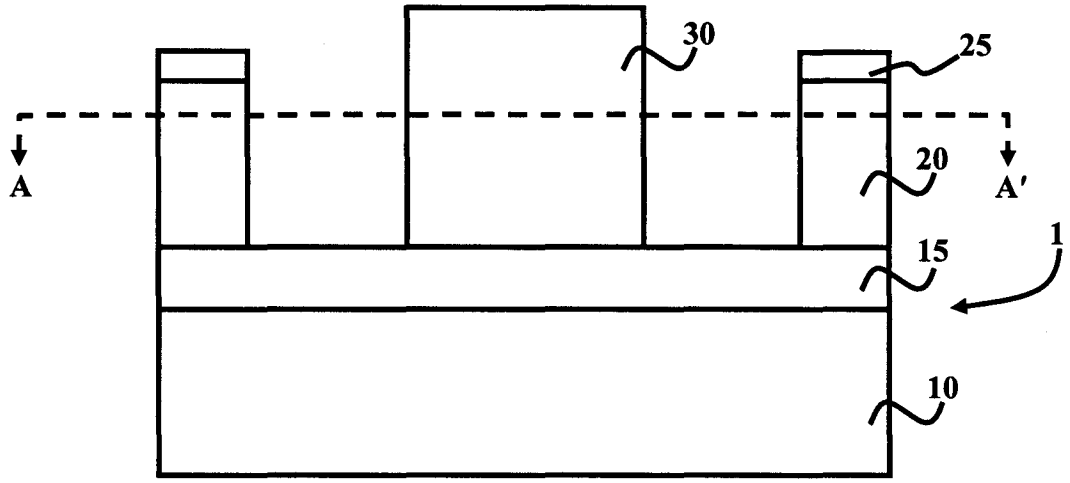


Figure 2 (Prior Art)

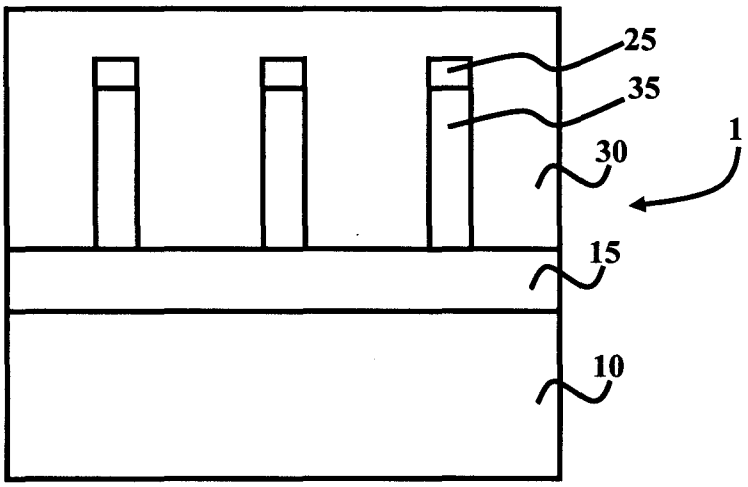


Figure 3

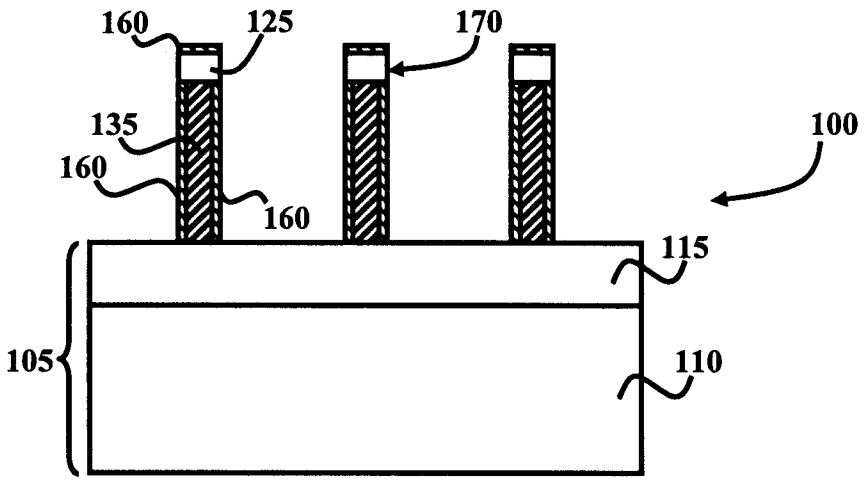


Figure 4

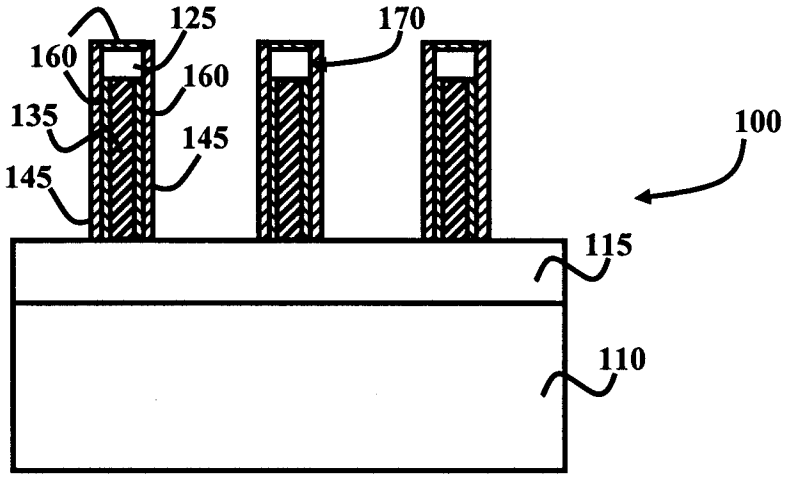


Figure 5

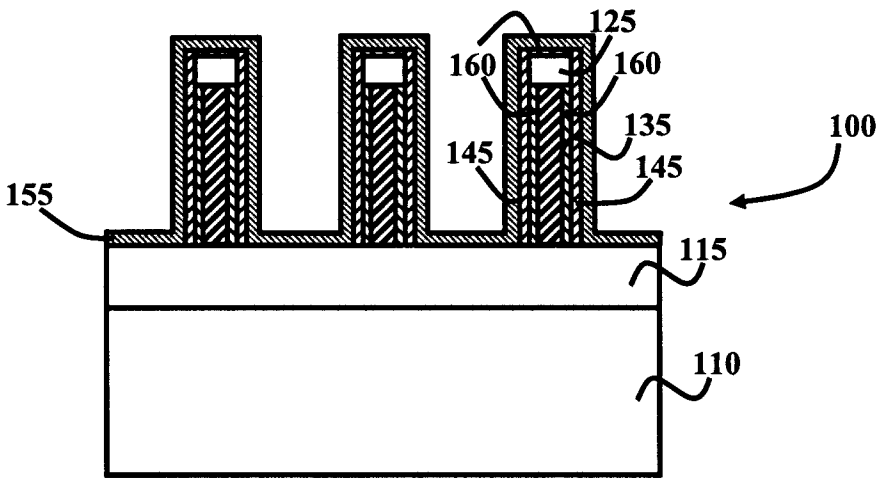


Figure 6

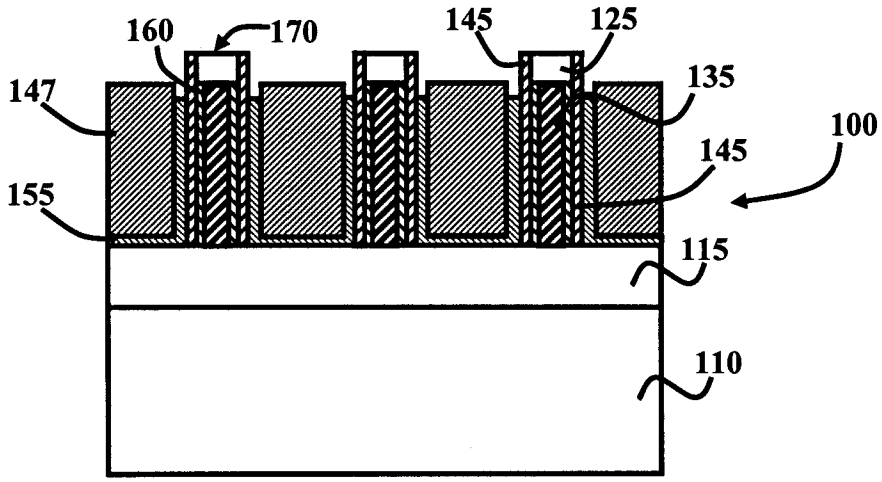


Figure 7

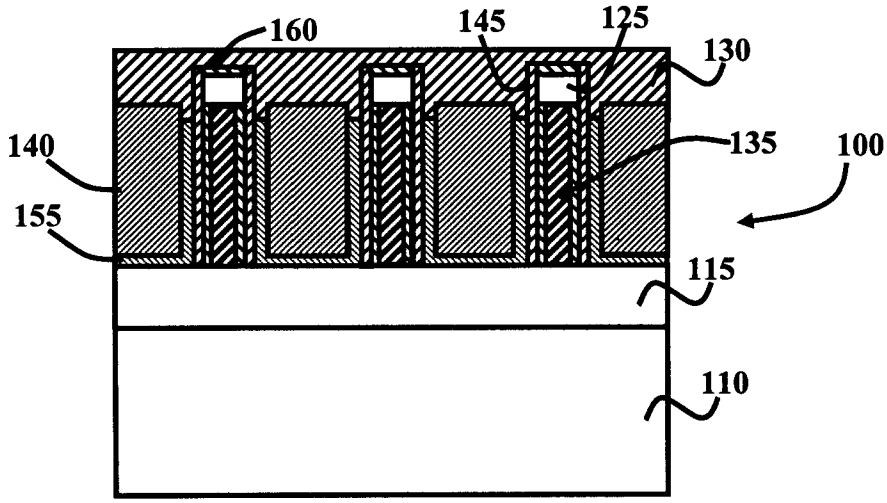


Figure 8

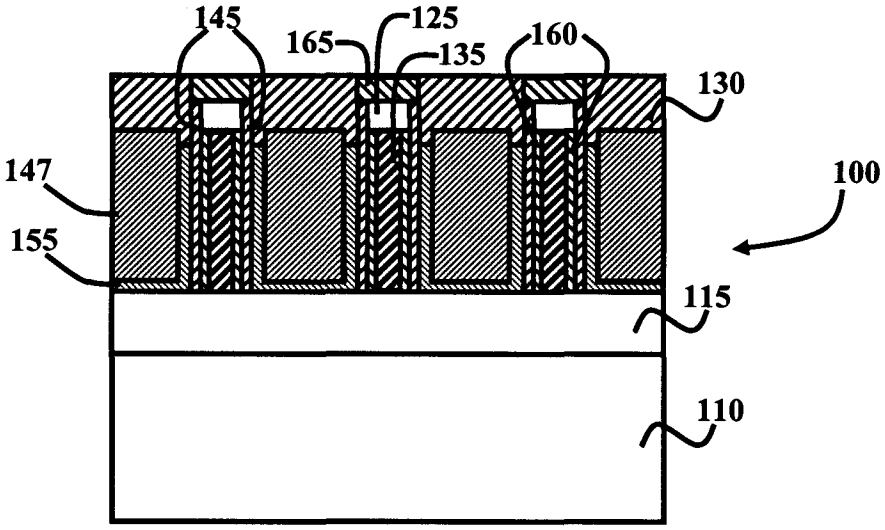


Figure 9

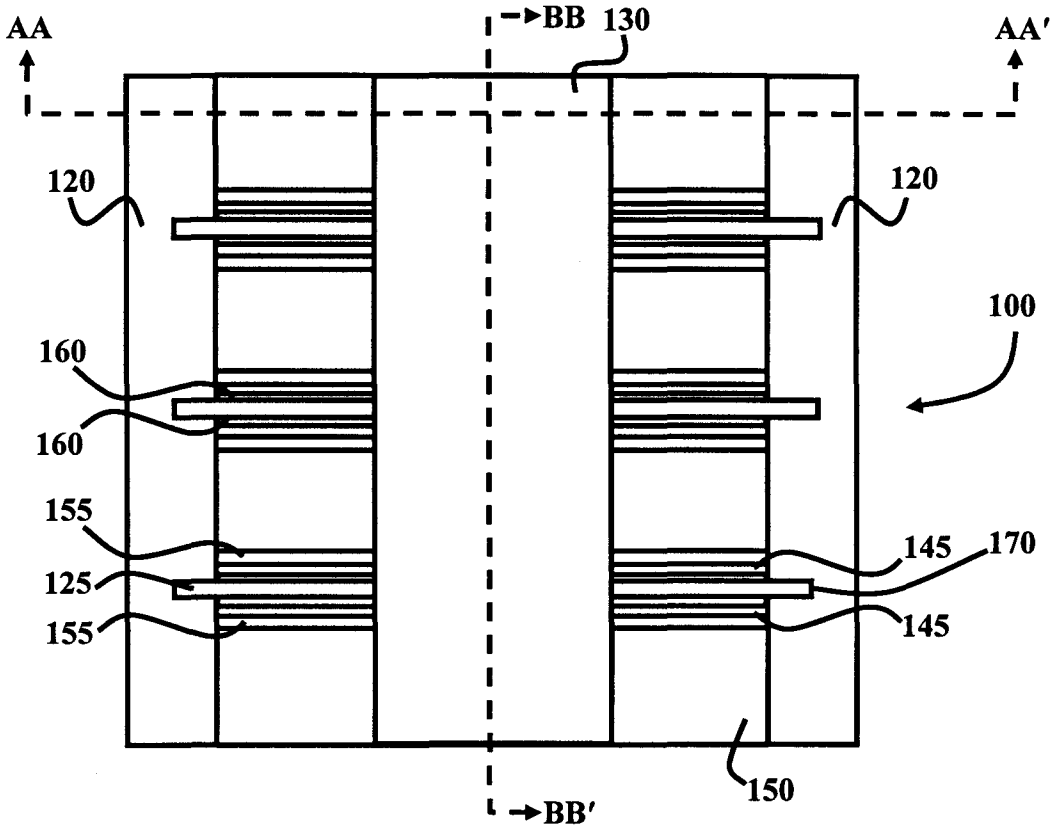


Figure 10(a)

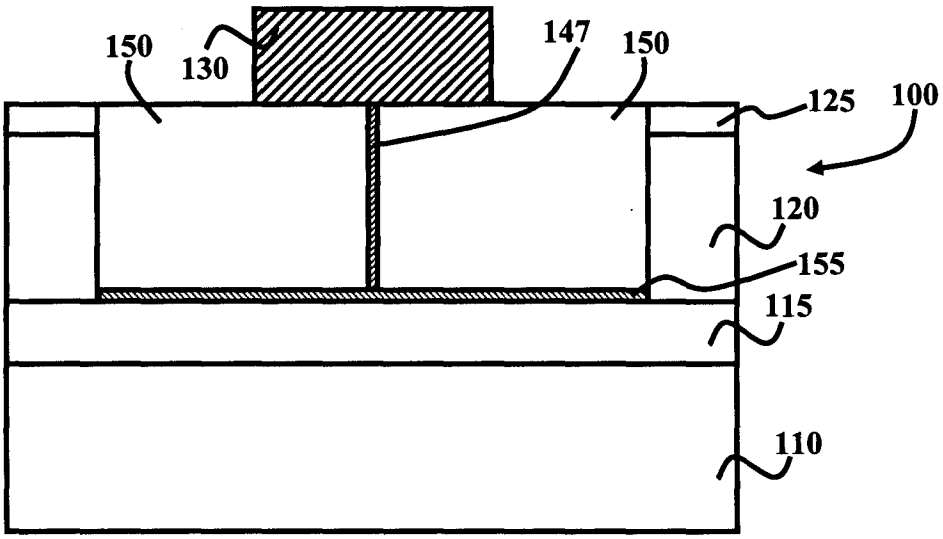


Figure 10(b)

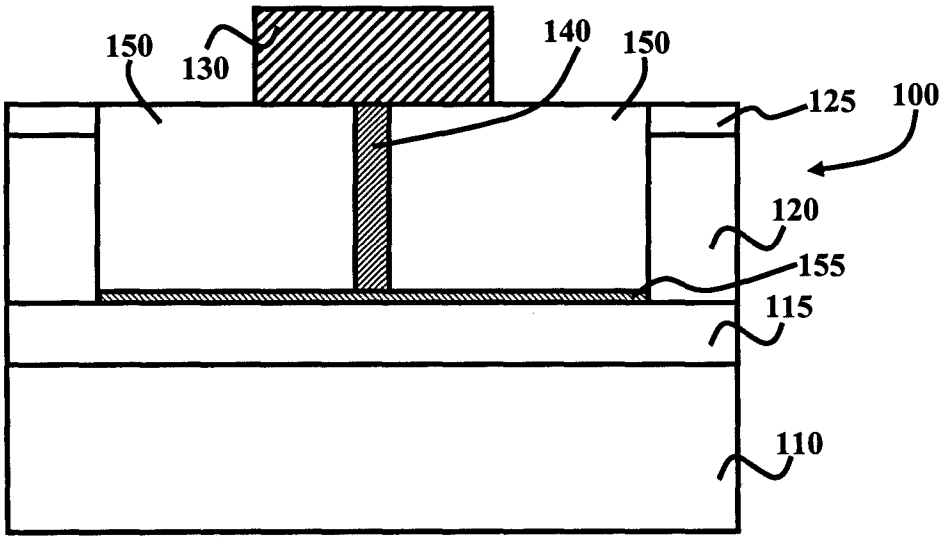


Figure 11(a)

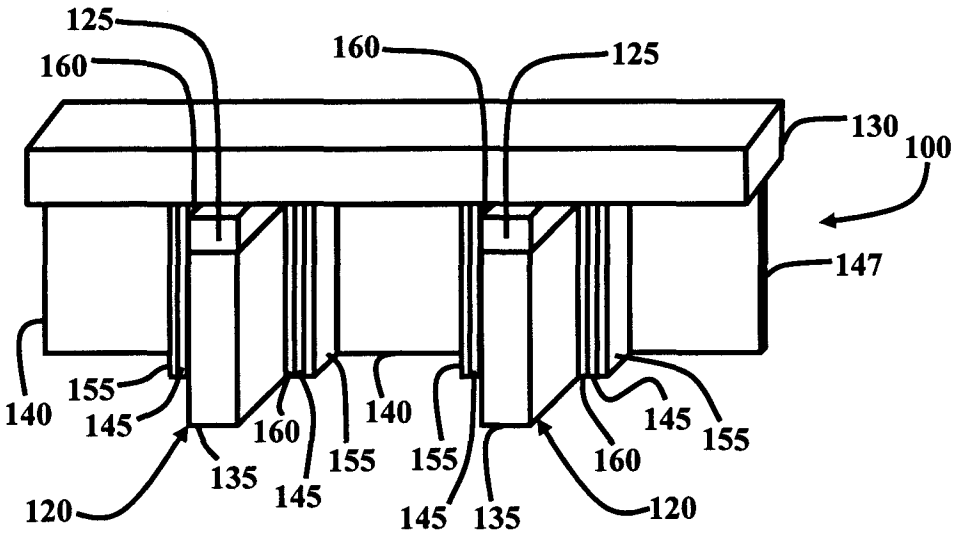


Figure 11(b)

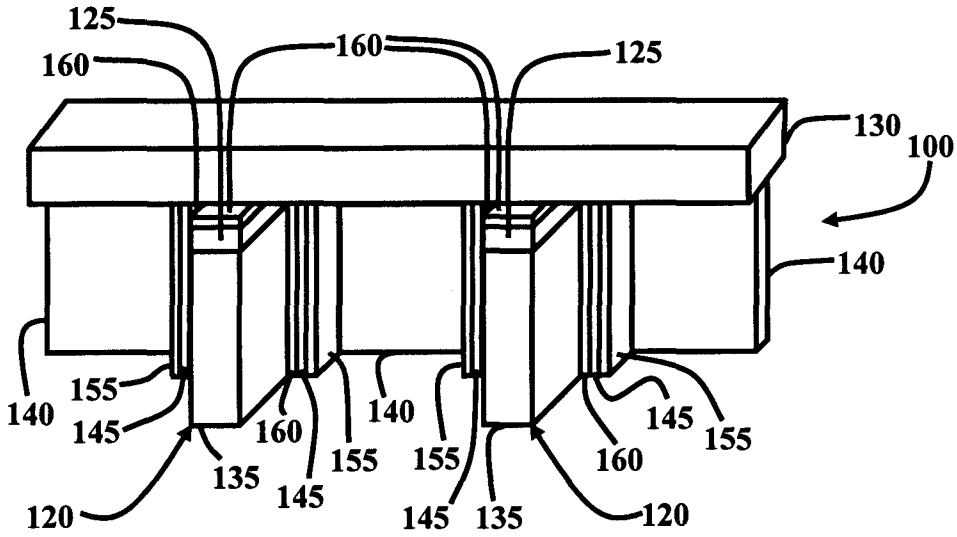


Figure 12(a)

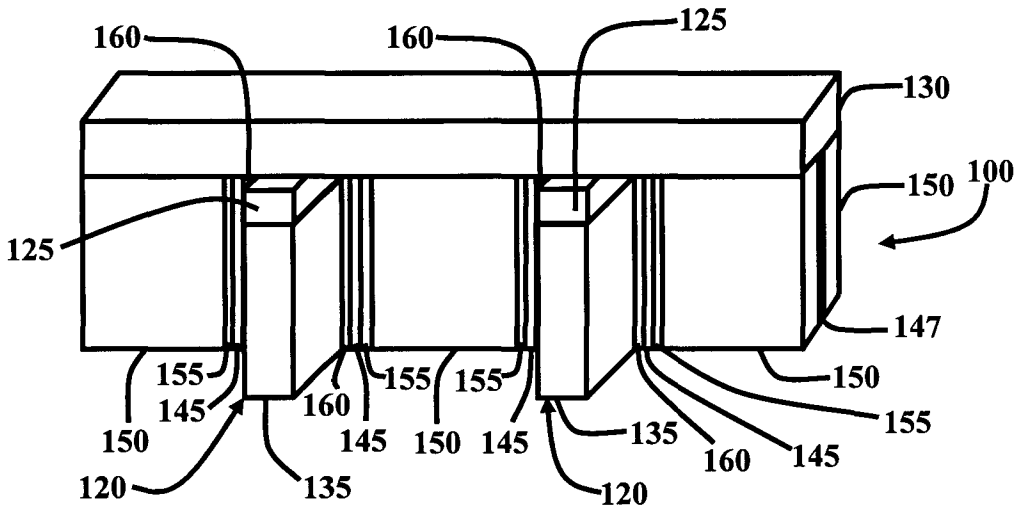


Figure 12(b)

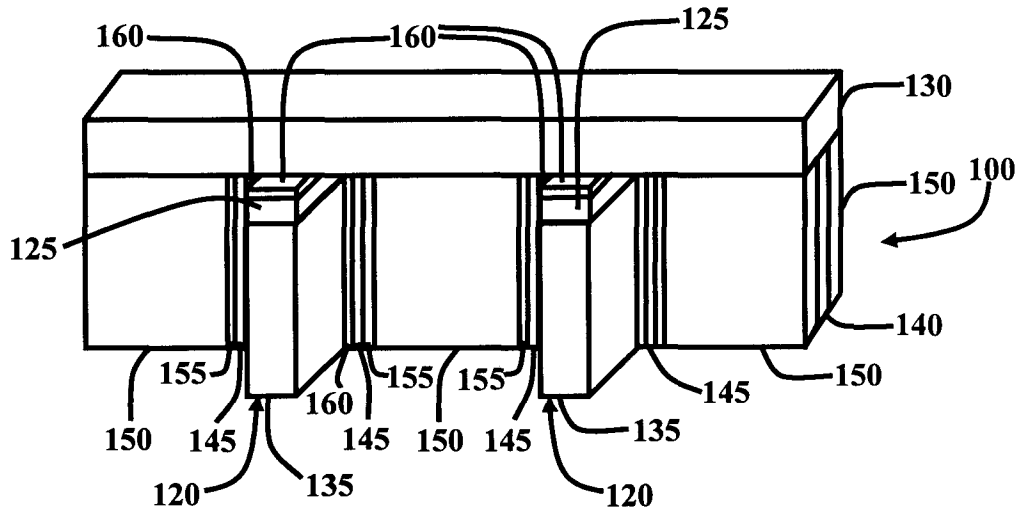
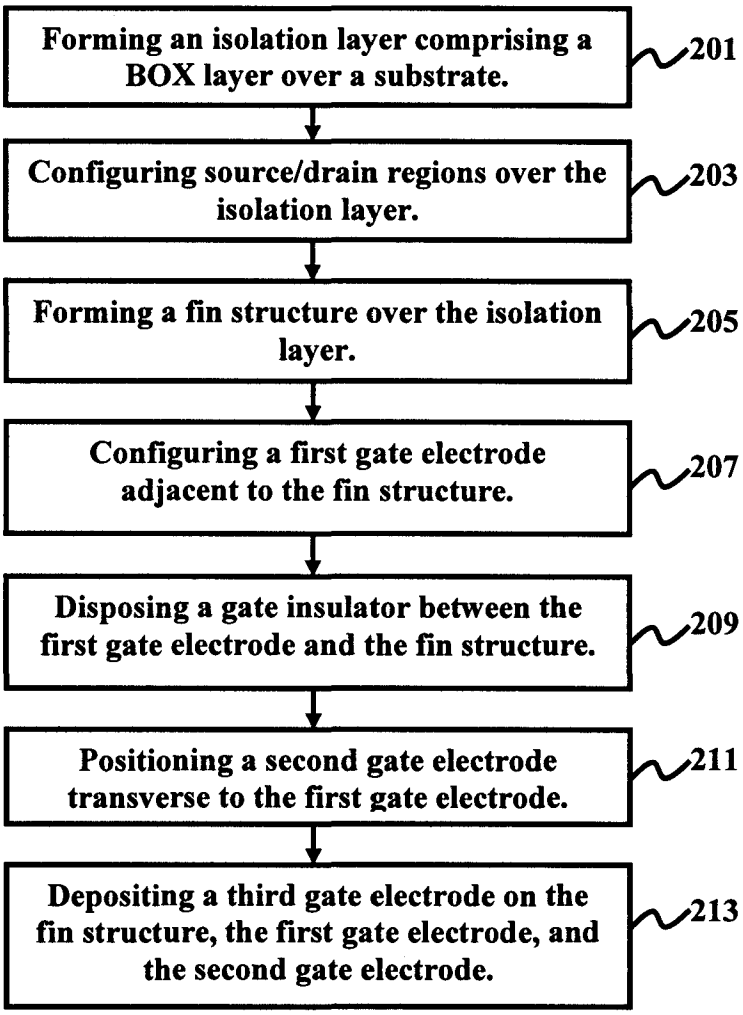


Figure 13


Forming an isolation layer comprising a BOX layer over a substrate.
201
Configuring source/drain regions over the isolation layer.
203
Forming a fin structure over the isolation layer.
205
Configuring a first gate electrode adjacent to the fin structure.
207
Disposing a gate insulator between the first gate electrode and the fin structure.
209
Positioning a second gate electrode transverse to the first gate electrode.
211
Depositing a third gate electrode on the fin structure, the first gate electrode, and the second gate electrode.
213